



1 of 4

FORM PTO-1449 U.S. PATENT & TRADEMARK OFFICE	SERIAL NO. 10/667,707	CASE NO. 9905/35
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b> (use several sheets if necessary)	FILING DATE September 22, 2003	GROUP ART UNIT 1765 APPLICANT(S): Moriceau et al.

## REFERENCE DESIGNATION

## **U.S. PATENT DOCUMENTS**

EXAMINER INITIAL	DOCUMENT NUMBER Number-Kind Code (if known)	DATE	NAME	CLASS/ SUBCLASS	FILING DATE
SA	C1 4,254,590	3/10/1981	Eisele et al.		
	C2 5,300,788	4/5/1994	Fan et al.		
	C3 5,400,458	3/28/1995	Rambosek		
	C4 5,811,348	9/22/1998	Matushita et al.		
	C5 5,877,070	3/2/1999	Goesele et al.		
	C6 5,909,627	6/1/1999	Egloff		
	C7 5,953,622	9/14/1999	Lée et al.		
	C8 5,994,207	11/30/1999	Henley et al.		
	C9 6,048,411	4/11/2000	Henley et al.		
	C10 6,054,370	4/25/2000	Doyle		
	C11 6,127,199	10/3/2000	Inoue		
	C12 6,146,979	11/14/2000	Henley et al.		
	C13 6,150,239	11/21/2000	Goesele et al.		
	C14 6,225,192	5/1/2001	Aspar et al.		
	C15 6,271,101	8/7/2001	Fukunaga		
	C16 6,303,468	10/16/2001	Aspar et al.		
	C17 6,323,108	11/27/2001	Kub et al.		
	C18 6,346,458	2/12/2002	Bower		
	C19 2002/0025604	2/28/2002	Tiwari		
	C20 6,362,077	3/26/2002	Aspar et al.		
	C21 2002/0153563	10/24/2002	Ogura		
	C22 2002/0185684	12/12/2002	Campbell et al.		
	C23 6,513,564	2/4/2003	Bryan et al.		
	C24 6,534,380	3/18/2003	Yamauchi et al.		
	C25 2003/0077885	4/24/2003	Aspar et al.		
	C26 6,593,212	7/15/2003	Kub et al.		
	C27 2003/0134489	7/17/2003	Schwarzenbach et al.		
	C28 6,607,969	8/19/2003	Kub et al.		
	C29 2003/0162367	8/28/2003	Roche		
	C30 2003/0199105	10/23/2003	Kub et al.		
	C31 6,727,549	4/27/2004	Doyle		
	C32 2004/0144487	7/29/2004	Martinez et al.		
	C33 6,770,507	8/3/2004	Abe et al.		
SA	C34 6,946,365	9/20/2005	Aspar et al.		

## FOREIGN PATENT DOCUMENTS

EXAMINER	/Shamim Ahmed/ (12/27/2006)	DATE CONSIDERED	12/27/2006
----------	-----------------------------	-----------------	------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609;  
Draw line through citation if not in conformance and not considered. Include copy of this form with next  
communication to applicant.

FORM PTO-1449		SERIAL NO. 10/667,707	CASE NO. 9905/35
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (use several sheets if necessary)		FILING DATE September 22, 2003	GROUP ART UNIT 1765
APPLICANT(S): Moriceau et al.			

EXAMINER INITIAL		DOCUMENT NUMBER Number-Kind Code (if known)	DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION YES OR NO
SA	C35	EP 0 293 049 B1	9/29/1993	Europe		
	C36	EP 0 410 679 A1	1/30/1991	Europe		
	C37	EP 0 786 801B1	6/18/2003	Europe		Abstract
	C38	EP 0 793 263 A2	9/3/1997	Europe		
	C39	EP 0 807 970 A1	11/19/1997	Europe		Abstract
	C40	EP 0 902 843 B1	3/29/2000	Europe		Abstract
	C41	EP 0 925 888 B1	11/10/2004	Europe		
	C42	EP 0 938 129 A1	8/25/1999	Europe		
	C43	EP 0 994 503 A1	4/19/2000	Europe		Abstract
	C44	EP 1 014 452 B1	5/3/2006	Europe		
	C45	EP 1 050 901 A2	11/8/2000	Europe		
	C46	FR 2 681 472 A1	3/19/1993	France		Abstract
	C47	FR 2 748 850 A1	11/21/1997	France		Abstract
	C48	FR 2 748 851 A1	11/21/1997	France		Abstract
	C49	FR 2 758 907 A1	7/31/1998	France		Abstract
	C50	FR 2 767 416 A1	2/19/1999	France		Abstract
	C51	FR 2 773 261 A1	7/2/1999	France		Abstract
	C52	FR 2 774 510 A1	8/6/1999	France		Abstract
	C53	FR 2 781 925 A1	2/4/2000	France		Abstract
	C54	FR 2 796 491 A1	1/19/01	France		Abstract
	C55	FR 2 797 347 A1	2/9/2001	France		Abstract
	C56	FR 2 809 867 A1	12/7/2001	France		Abstract
	C57	FR 2 847 075 A1	5/14/2004	France		Abstract
	C58	JP 62265717	11/18/1987	Japan		Abstract
	C59	JP 01004013	09/01/1989	Japan		Abstract
	C60	JP 7302889	11/14/1995	Japan		Abstract
	C61	JP 11045862	2/16/1999	Japan		Abstract
	C62	JP 11074208	3/16/1999	Japan		Abstract
	C63	JP 11087668	3/30/1999	Japan		Abstract
	C64	JP 11233449	8/27/1999	Japan		Abstract
	C65	WO 99/08316 A1	2/18/1999	WIPO		Abstract
	C66	WO 99/35674 A1	7/15/1999	WIPO		Abstract
	C67	WO 99/39378 A1	8/5/1999	WIPO		
	C68	WO 00/48238 A1	8/17/2000	WIPO		Abstract
	C69	WO 00/63965 A1	10/26/2000	WIPO		
	C70	WO 01/11930A2	2/15/2001	WIPO		
	C71	WO 02/47156 A1	6/13/2002	WIPO		Abstract
	C72	WO 02/083387 A1	10/24/2002	WIPO		Abstract
SA	C73	WO 03/013815 A1	2/20/2003	WIPO		Abstract

EXAMINER /Shamim Ahmed/ (12/27/2006)	DATE CONSIDERED 12/27/2006
---	-------------------------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609;  
Draw line through citation if not in conformance and not considered. Include copy of this form with next  
communication to applicant.

FORM PTO-1449	SERIAL NO. 10/667,707	CASE NO. 9905/35
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (use several sheets if necessary)	FILING DATE September 22, 2003	GROUP ART UNIT 1765
APPLICANT(S): Moriceau et al.		

## FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER Number-Kind Code (if known)	DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION YES OR NO
C74	WO 2004/044976	5/27/2004	WIPO		Abstract

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)				
	C75	Agarwal et al "Efficient production of Silicon-on-insulator films by co-implatation of HE <sup>+</sup> with H <sup>+</sup> ", <i>Applied Physics Letter</i> , American Institute of Physics, Vol. 72, No. 9, March 1998, pp. 1086-1088			
SA	C76	Bruel et al., [Vol. 99-1] Meeting Abstract No. 333, "Single-crystal semiconductor layer delamination and transfer through hydrogen implantation," <i>The 195th Meeting of The Electrochemical Society</i> , May 2-6, 1999, Seattle, Washington			
	C77	Camperi-Ginestet et al., "Alignable Epitaxial Lift-off of GaAs Materials with Selective Deposition Using Polyimide Diaphragms", <i>IEEE Transactions Photonics Technology Letters</i> , Vol. 3, No. 12, December 1991, pp. 1123-1126			
	C78	Cerofolini et al. "Ultradense Gas Bubbles in Hydrogen-or-Helium-Implanted (or Co-implanted) Silicon", <i>Materials Science and Engineering</i> , B71, 2000, pp. 196-202			
	C79	Demeester, et al., "Epitaxial Lift-off and its Applications", <i>Semicond. Sci. Technol.</i> , Vol. 8, 1993, pp. 1124-1135			
	C80	DiCioccio et al., "III-V layer transfer onto silicon and applications", <i>Phys. Stat. Sol. (a)</i> , Vol. 202, No. 4., 2005, pp. 509-515/DOI 10.1002/pssa. 200460411			
	C81	Feijoo et al., "Prestressing of Bonded Wafers", Vol. 92-7 1992 pp. 230-238			
	C82	Feng et al., "Generalized Formula for Curvature Radius and Layer Stresses Caused by Thermal Strain in Semiconductor Multilayer Structures", <i>J. Appl. Phys.</i> , Vol. 54, No. 1, 1983, pp. 83-85			
	C83	Hamaguchi, et al., "Novel LSI/SOI Wafer Fabrication Using Device Layer Transfer Technique" <i>Proc. IEDM</i> , 1985, pp. 688-691			
	C84	Henttinen et al. "Mechanically induced Si Layer Transfer in Hydrogen-Implanted Si-Wafers", <i>American Institute of Physics</i> , Vol. 76, No. 17, April 2000, pp. 2370-2372			
	C85	Kucheyev et al., "Ion implantation into GaN", <i>Materials Science and Engineering</i> , 33, 2001, pp. 51-107			
	C86	Liu et al., "Ion implantation in GaN at liquid-nitrogen temperature: Structural characteristics and amorphization," <i>Physical Review B of The American Physical Society</i> , Vol. 57, No. 4, 1988, pp. 2530-2535			
↓	C87	Moriceau et al., [Vol. 99-1] Meeting Abstract No. 405, "A New Characterization Process Used to Qualify SOI Films," <i>The 195th Meeting of The Electrochemical Society</i> , May 2-6, 1999, Seattle, Washington.			
SA	C88	Pollentier et al., "Fabrication of High-Radiance LEDs by Epitaxial Lift-off" <i>SPIE</i> , Vol. 1361, 1990, pp. 1056-1062			

EXAMINER /Shamim Ahmed/ (12/27/2006)	DATE CONSIDERED 12/27/2006
---	-------------------------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/667,707	CASE NO. 9905/35
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (use several sheets if necessary)	FILING DATE September 22, 2003	GROUP ART UNIT 1765
APPLICANT(S): Moriceau et al.		

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
SA	C89	Suzuki et al., "High-Speed and Low Power n <sup>+</sup> -p <sup>+</sup> Double-Gate SOI CMOS", <i>IEICE Trans. Electron.</i> , Vol. E78-C, No. 4, April 1995, pp. 360-367
	C90	Timoshenko, S., "Analysis of Bi-Metal Thermostats", <i>J. Opt. Soc. Am.</i> , 11, 1925, pp. 233-256
	C91	Wong et al., "Integration of GaN Thin Films with Dissimilar Substrate Materials by Pd-In Metal Bonding and Laser Lift-off", <i>Journal of Electronic Materials</i> , Vol. 28, No. 12, 1999, pp. 1409-1413
↓	C92	Yun et al., "Fractional Implantation Area Effects on Patterned Ion-Cut Silicon Layer Transfer," Dept. of Electrical Eng. And Computer Sciences, University of California, Berkeley, CA 94720, USA, 1999 IEEE International SOI Conference, Oct. 1999, pg. 129-30
SA	C93	Yun et al., "Thermal and Mechanical Separations of Silicon Layers from Hydrogen Pattern-Implanted Wafers," <i>Journal of Electronic Materials</i> , Vol. No. 36, No. 8 2001

EXAMINER /Shamim Ahmed/ (12/27/2006)	DATE CONSIDERED 12/27/2006
---	-------------------------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.